

**SANYO**

No.3179A

**2SA1763**

PNP Epitaxial Planar Silicon Transistor

High-Speed Switching Applications

**Features**

- Fast switching speed
- Low collector saturation voltage
- High gain-bandwidth product
- Small collector capacitance
- Very small-sized package permitting the 2SA1763-applied sets to be made small and slim
- Complementary pair with the 2SC4452

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector to Base Voltage	$V_{CBO}$	-15	V
Collector to Emitter Voltage	$V_{CEO}$	-15	V
Emitter to Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-200	mA
Collector Current(Pulse)	$I_{CP}$	-500	mA
Base Current	$I_B$	-40	mA
Collector Dissipation	$P_C$	150	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

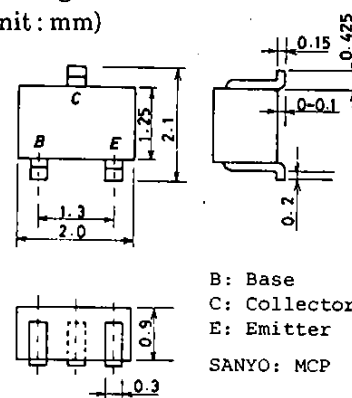
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -8V, I_E = 0$			-0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = -3V, I_C = 0$			-0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = -1V, I_C = -10mA$	50	80	140	
Gain-Bandwidth Product	$f_T$	$V_{CE} = -10V, I_C = -10mA$	450	1000		MHz
Output Capacitance	$c_{ob}$	$V_{CB} = -5V, f = 1MHz$		1.8	3.0	pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$		-0.07	-0.20	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -1mA$		-0.80	-0.85	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Turn-ON Time	$t_{on}$	See specified Test Circuit.		11		ns
Storage Time	$t_{stg}$	"		21		ns
Turn-OFF Time	$t_{off}$	"		19		ns

Marking : FS

For the specified switching test circuit, see the next page.

**Package Dimensions 2059**

(unit : mm)

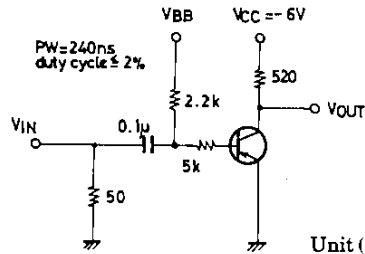
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7290MH(KOTO)/6279MO, TS No.3179-1/4

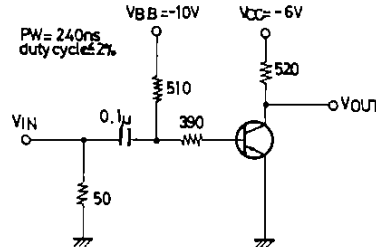
Switching Time Test Circuits

$t_{on}, t_{off}$  Test Circuit



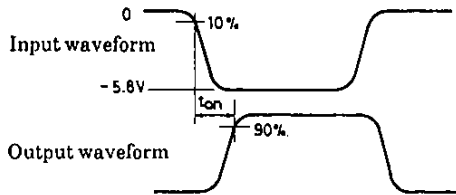
Unit (Resistance :  $\Omega$ ,  
Capacitance : F)

$t_{stg}$  Test Circuit

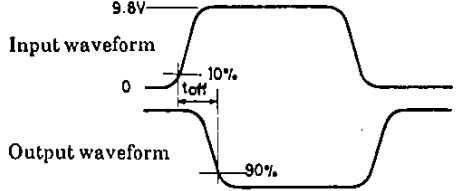


Unit (Resistance :  $\Omega$ , Capacitance : F)

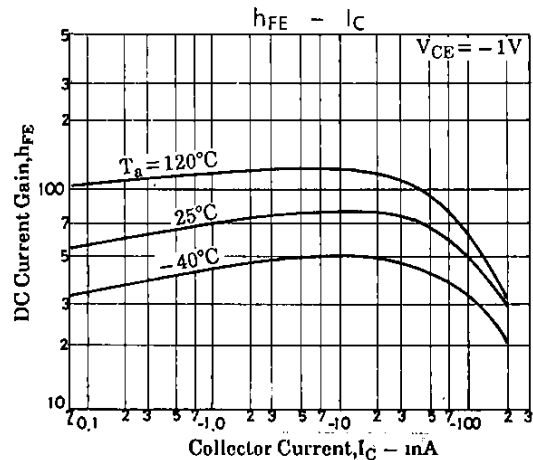
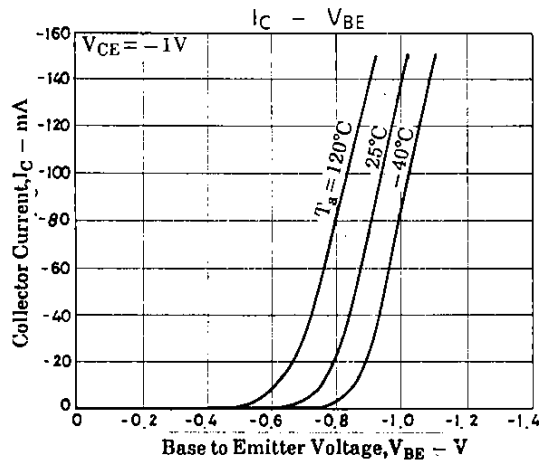
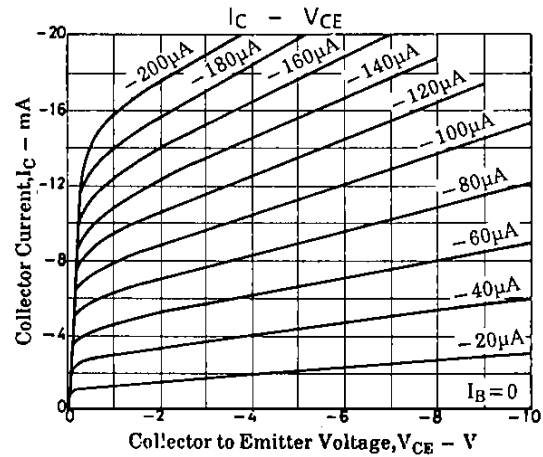
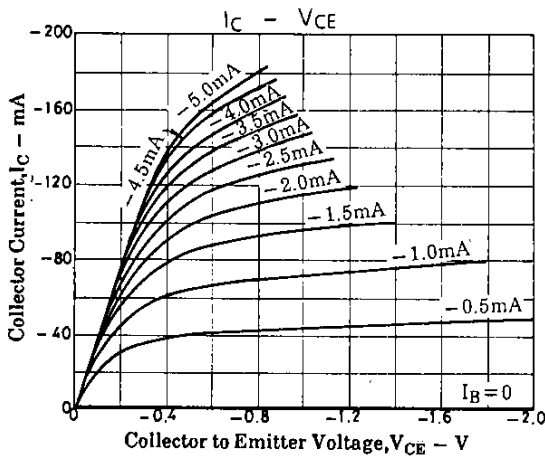
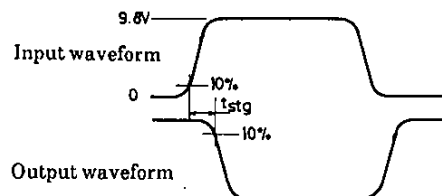
$t_{on}$  Test Waveform ( $V_{BB} = GND$ )



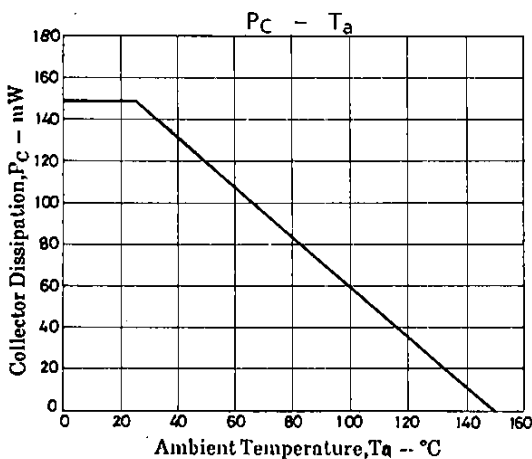
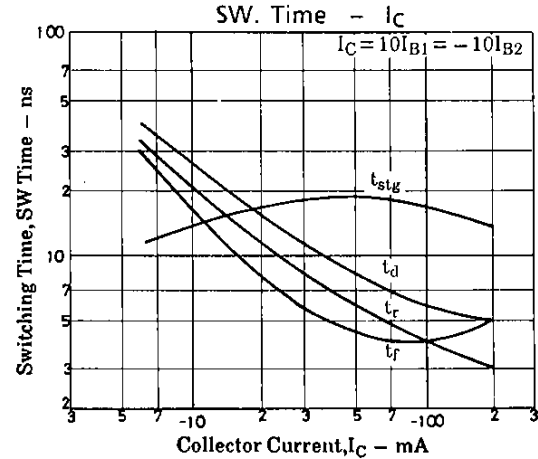
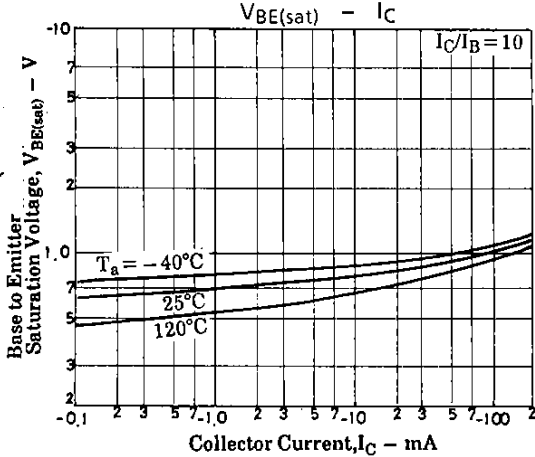
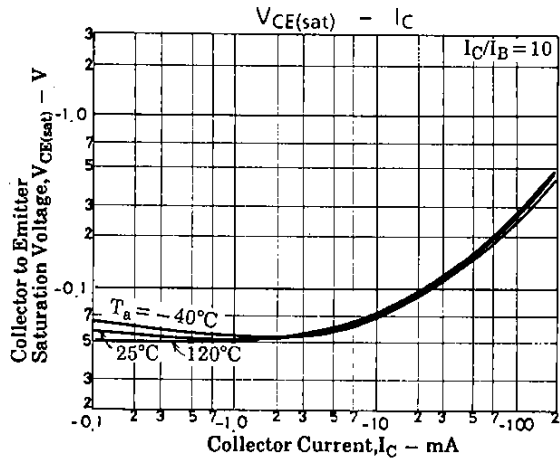
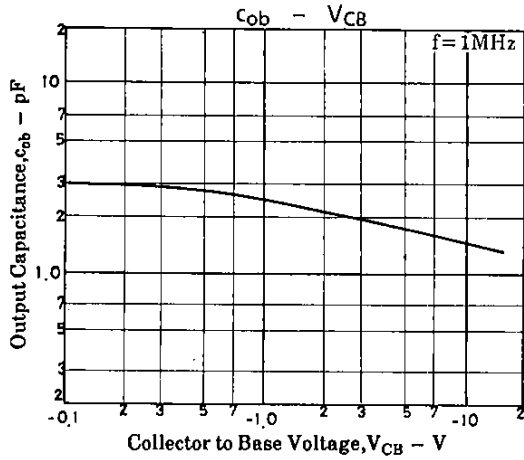
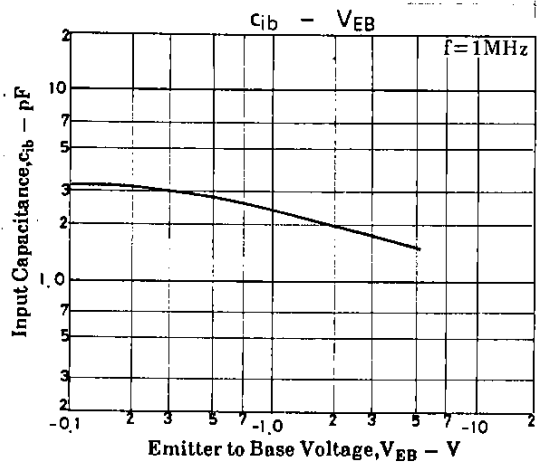
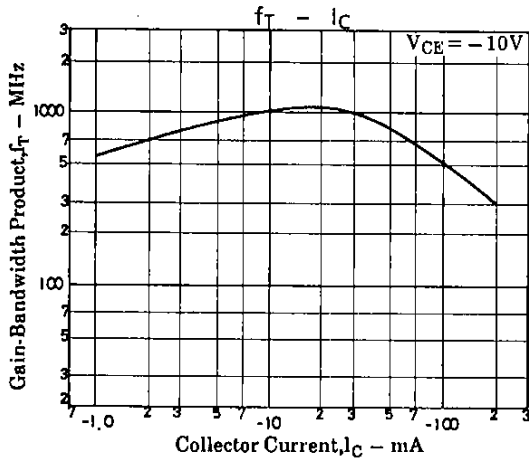
$t_{off}$  Test Waveform ( $V_{BB} = -8.0V$ )



$t_{stg}$  Test Waveform



# 2SA1763



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